

# APPLICATION DATA SHEET

## Application Information

Application Type:: Regular  
Subject Matter:: Utility  
Title:: SILICON ON INSULATOR STRUCTURE  
FROM LOW DEFECT DENSITY SINGLE  
CRYSTAL SILICON  
Attorney Docket Number:: MEMC 98-3052 (2512.2)  
Request for Early Publication?:: No  
Request for Non-Publication?:: No  
Total Drawing Sheets:: 35  
Small Entity?:: No  
Petition Included?:: No  
Secrecy Order in Parent?:: No

## Applicant Information

Applicant Authority Type:: Inventor  
Primary Citizenship Country:: US  
Status:: Full Capacity  
Given Name:: Robert  
Middle Name:: J.  
Family Name:: Falster  
City of Residence:: London  
Country of Residence:: England  
Street of Mailing Address:: 508 Pearl Drive, P.O. Box 8  
City of Mailing Address:: St. Peters  
State or Province of Mailing  
Address:: MO  
Postal Code of Mailing Address:: 63376

## Correspondence Information

Correspondence Customer Number:: 000321

**Representative Information**

Representative Customer Number:: 000321

**Domestic Priority Information**

Application::	Continuity Type::	Parent Application::	Parent Filing Date::
This application	Division of	09/737,715	12/15/00
09/737,715	Continuation of	09/387,288	08/31/99
09/387,288	Non- Provisional of	60/098,902	09/02/98

**Assignee Information**

Assignee Name:: MEMC Electronic Materials, Inc.